

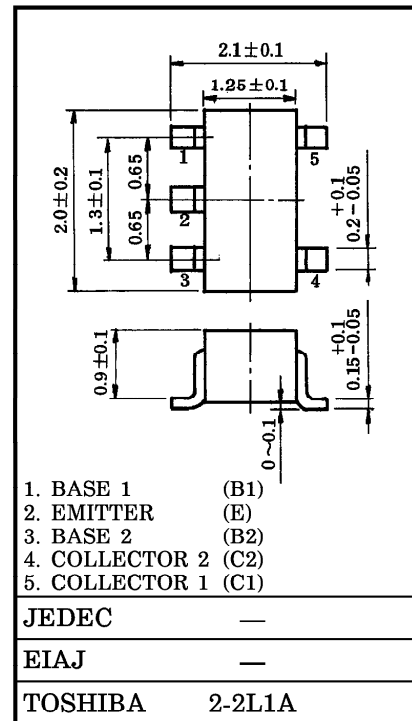
TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1873

AUDIO FREQUENCY GENERAL PURPOSE AMPLIFIER APPLICATIONS.

- Small Package (Dual Type)
- High Voltage and High Current
: $V_{CEO} = -50V$, $I_C = -150mA$ (MAX.)
- High h_{FE}
- Excellent h_{FE} Linearity
: $h_{FE}(I_C = -0.1mA) / h_{FE}(I_C = -2mA) = 0.95$ (Typ.)
- Complementary to 2SC4944

Unit in mm

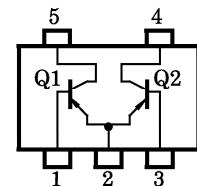


- 1. BASE 1 (B1)
- 2. EMITTER (E)
- 3. BASE 2 (B2)
- 4. COLLECTOR 2 (C2)
- 5. COLLECTOR 1 (C1)

JEDEC	—
EIAJ	—
TOSHIBA	2-2L1A

Weight : 6.2mg

EQUIVALENT CIRCUIT (TOP VIEW)



MAXIMUM RATINGS (Ta = 25°C) (Q1, Q2 COMMON)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-150	mA
Base Current	I_B	-30	mA
Collector Power Dissipation	P_C *	200	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-55~125	°C

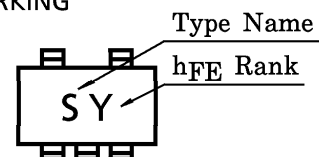
* Total Rating

ELECTRICAL CHARACTERISTIC (Ta = 25°C) (Q1, Q2 COMMON)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -50V, I_E = 0$	—	—	-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-0.1	μA
DC Current Gain	h_{FE} (Note)	$V_{CE} = -6V, I_C = -2mA$	120	—	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$	—	-0.1	-0.3	V
Transition Frequency	f_T	$V_{CE} = -10V, I_C = -1mA$	80	—	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	4	7	pF

Note : h_{FE} Classification
 Y (Y) : 120~240, (GR) (G) : 200~400
 () Marking Symbol

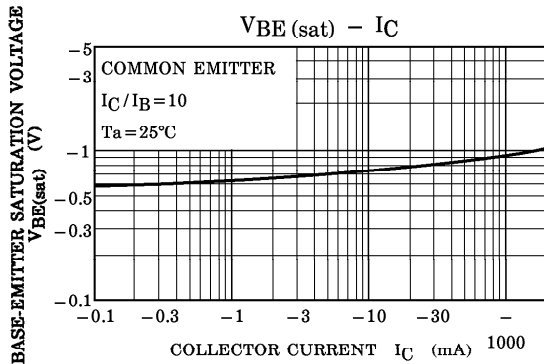
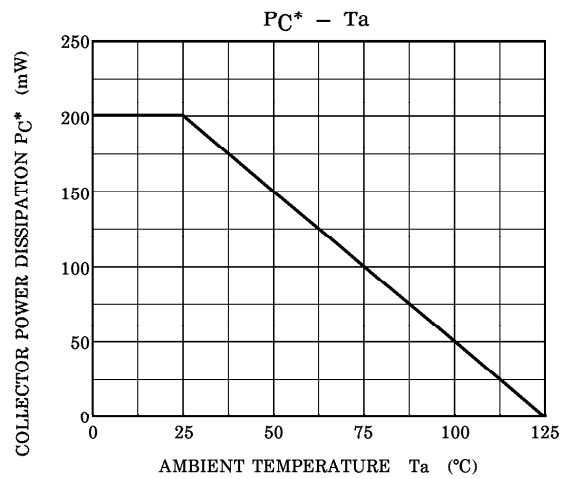
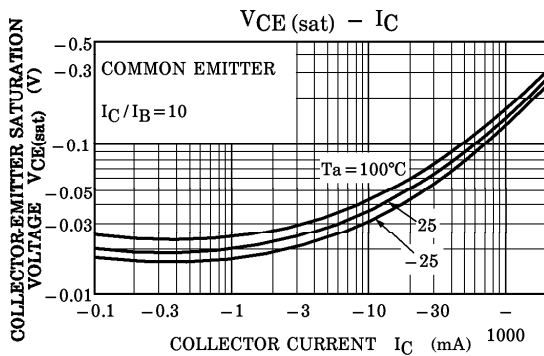
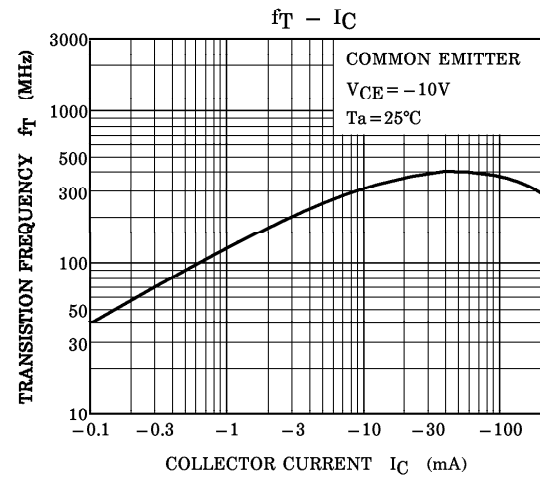
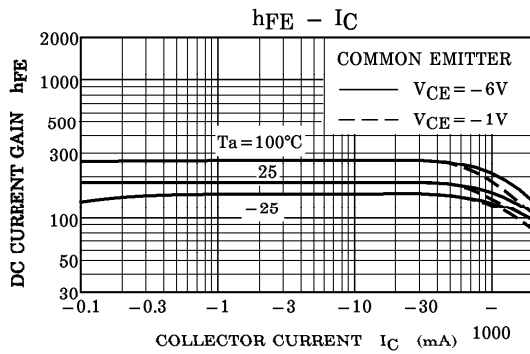
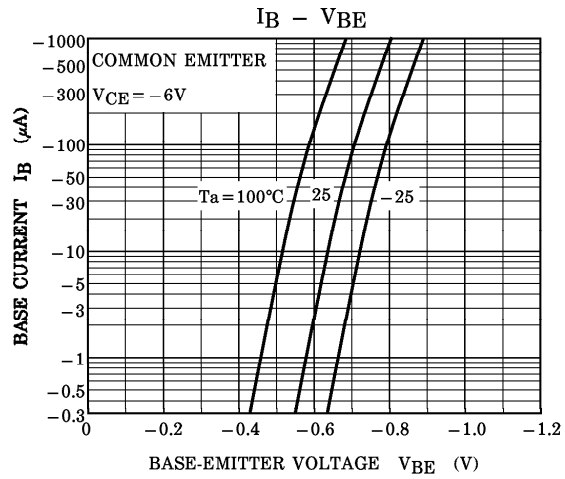
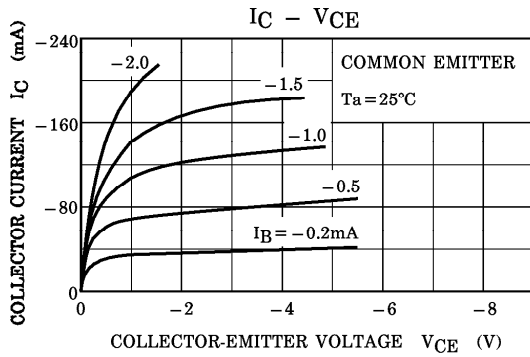
MARKING



961001EAA2

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(Q1, Q2 COMMON)



* : Total Rating

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